

ISC Silicon NPN Power Transistor

2SC2260

DESCRIPTION

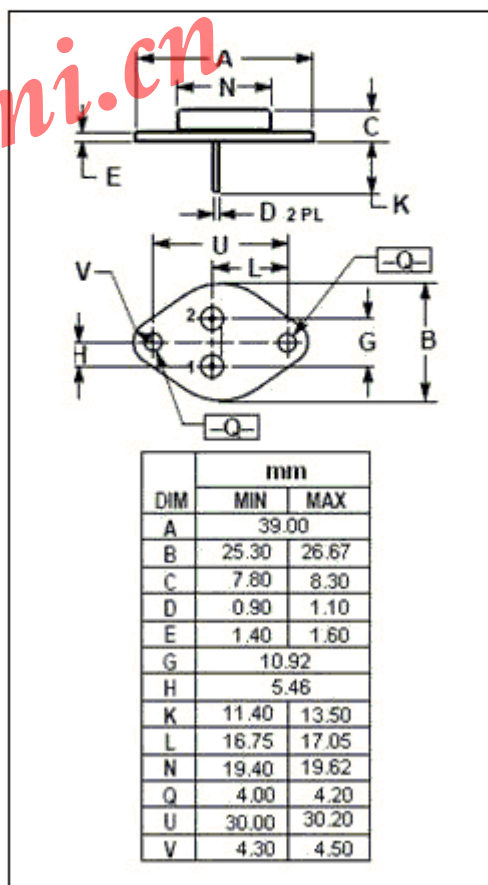
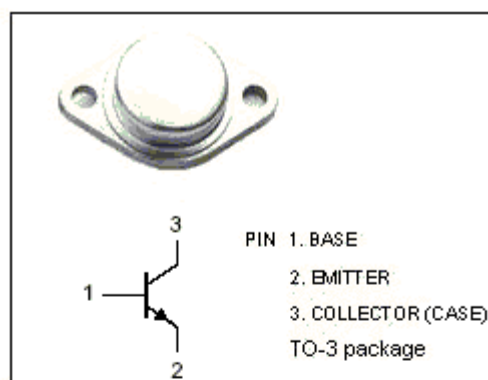
- High Power Dissipation-
: $P_C = 80W(\text{Max.})@T_C=25^\circ\text{C}$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 100V(\text{Min.})$
- Complement to Type 2SA980

APPLICATIONS

- Designed for general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	160	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	8	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	80	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 $T_j=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}$; $I_B=0$	100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}$; $I_B=0.3\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=160\text{V}$; $I_E=0$			1.0	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}$; $I_C=0$			1.0	mA
h_{FE}	DC Current Gain	$I_C=3\text{A}$; $V_{CE}=4\text{V}$	30			
f_T	Current-Gain—Bandwidth Product	$I_E=-0.5\text{A}$; $V_{CE}=12\text{V}$		15		MHz

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